

NVJS4151P

MOSFET – Power, Single P-Channel, Trench, SC-88 -20 V, -4.1 A

Features

- Leading Trench Technology for Low $R_{DS(ON)}$ Extending Battery Life
- SC-88 Small Outline (2x2 mm) for Maximum Circuit Board Utilization, Same as SC-70-6
- Gate Diodes for ESD Protection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	-20	V	
Gate-to-Source Voltage		V_{GS}	± 12	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-3.2	A
			$T_A = 85^\circ\text{C}$	-2.3	
	$t \leq 5\text{ s}$	$T_A = 25^\circ\text{C}$	-4.1		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.2	W
Pulsed Drain Current		$t_p = 10\ \mu\text{s}$	I_{DM}	-13	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	-0.8	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	
ESD	Human Body Model (HBM)	ESD	4000	V	

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5\text{ s}$	$R_{\theta JA}$	75	
Junction-to-Lead – Steady State	$R_{\theta JL}$	45	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

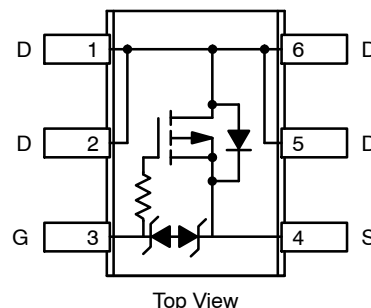


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
-20 V	55 m Ω @ -4.5 V	-4.1 A
	70 m Ω @ -2.5 V	
	180 m Ω @ -1.8 V	

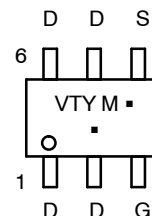
SC-88 (SOT-363)



MARKING DIAGRAM & PIN ASSIGNMENT



SC-88/SOT-363
CASE 419B



VTY = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NVJS4151PT1G	SC-88 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVJS4151P

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J		-12			mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = -16 V, V _{DS} = 0 V	T _J = 25°C		-1.0	μA
			T _J = 85°C		-5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1.5	μA
		V _{DS} = 0 V, V _{GS} = ±12 V			±10	mA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-0.40		-1.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J		4.0			mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -2.9 A		55	67	mΩ
		V _{GS} = -2.5 V, I _D = -2.4 A		70	85	
		V _{GS} = -1.8 V, I _D = -1.0 A		180	205	
Forward Transconductance	g _{FS}	V _{GS} = -10 V, I _D = -3.3 A		12		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -10 V		850		pF
Output Capacitance	C _{OSS}			160		
Reverse Transfer Capacitance	C _{RSS}			110		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -3.3 A		10		nC
Gate-to-Source Charge	Q _{GS}			1.5		
Gate-to-Drain Charge	Q _{GD}			2.8		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -4.5 V, V _{DD} = -10 V, I _D = -1.0 A, R _G = 6.0 Ω		0.85		μs
Rise Time	t _r			1.7		
Turn-Off Delay Time	t _{d(OFF)}			2.7		
Fall Time	t _f			4.2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -1.3 A, T _J = 25°C		-0.75	-1.2	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = -1.3 A		63		ns
Charge Time	T _a			9.0		
Discharge Time	T _b			54		
Reverse Recovery Charge	Q _{RR}			0.23		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL ELECTRICAL CHARACTERISTICS

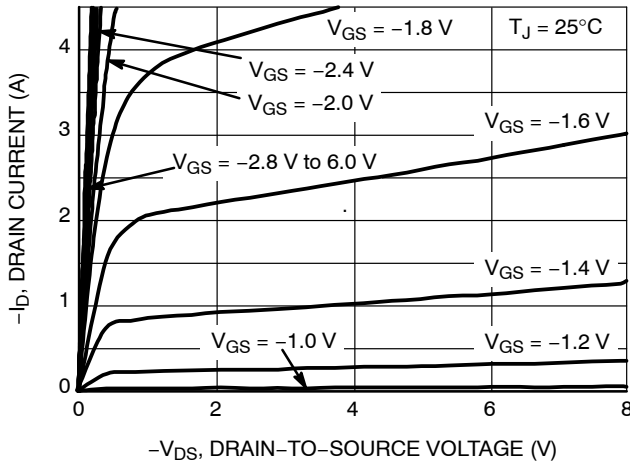


Figure 1. On-Region Characteristics

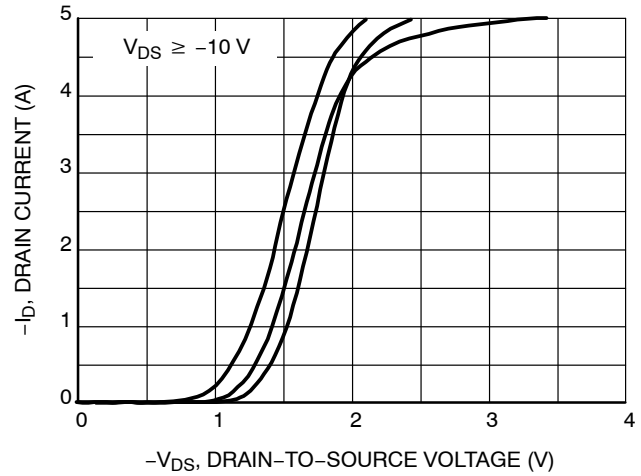


Figure 2. On-Region Characteristics

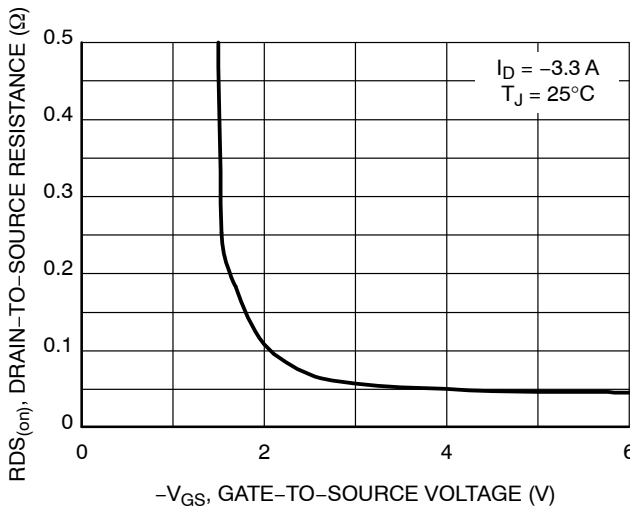


Figure 3. On-Resistance versus Gate-to-Source Voltage

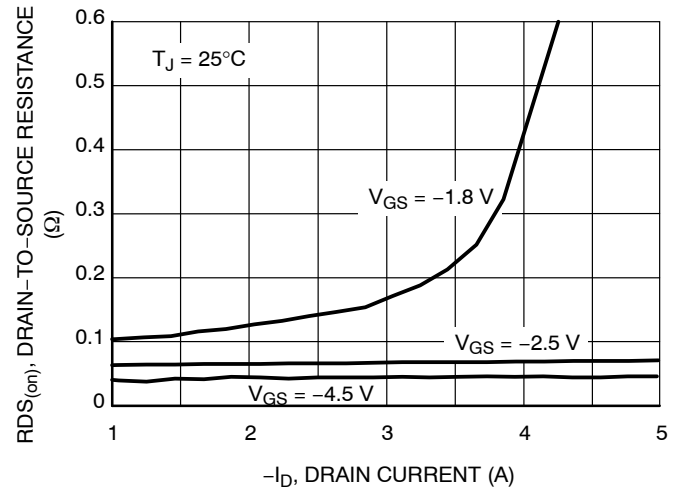


Figure 4. On-Resistance versus Drain Current and Gate Voltage

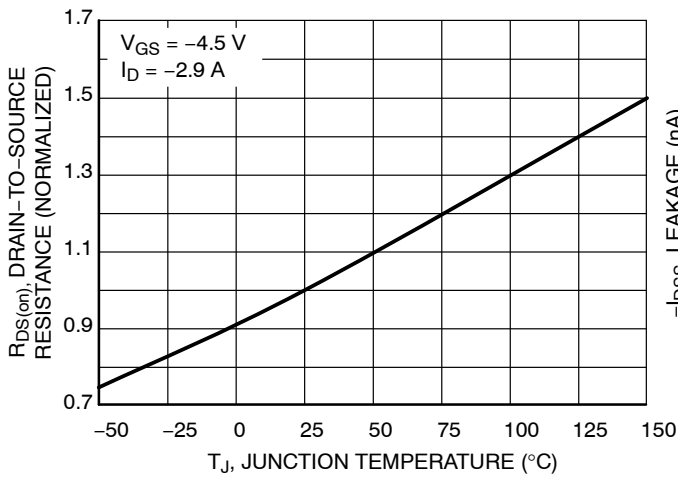


Figure 5. On-Resistance Variation with Temperature

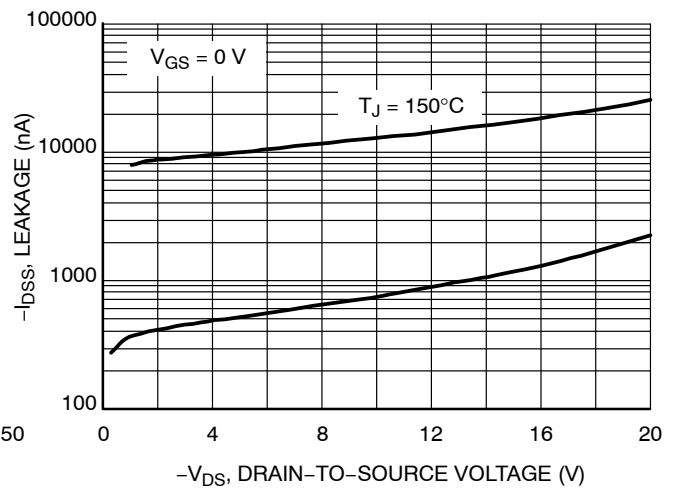


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

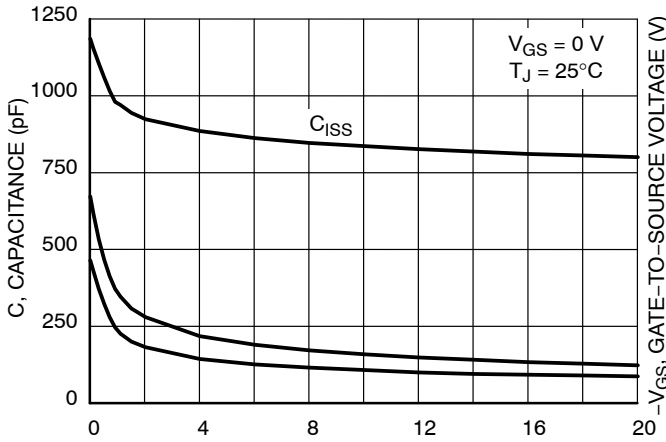


Figure 7. Capacitance Variation

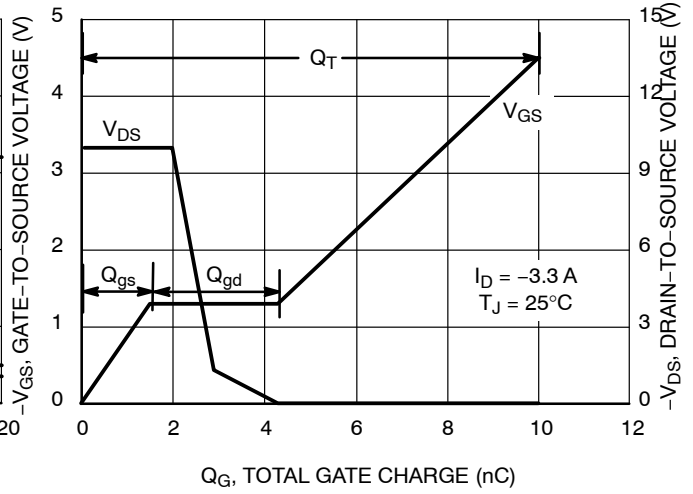


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

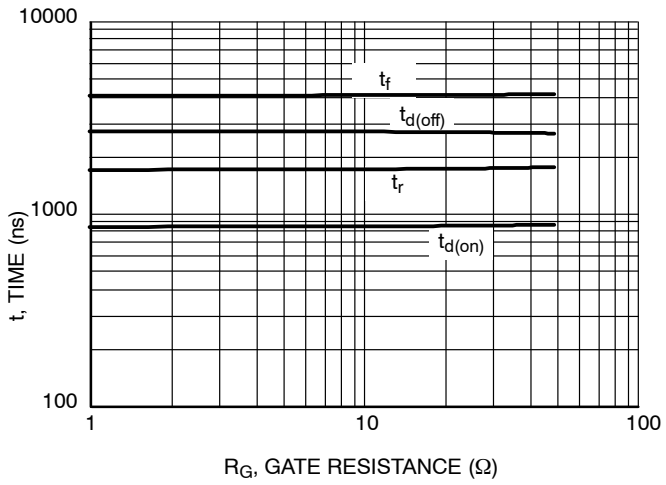


Figure 9. Resistive Switching Time Variation Gate Resistance

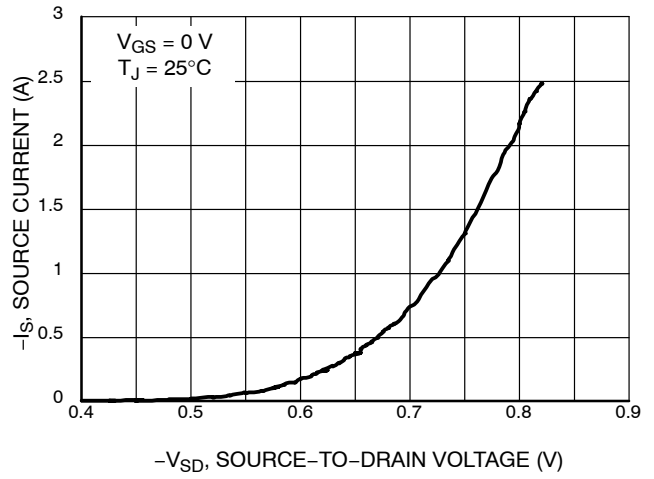
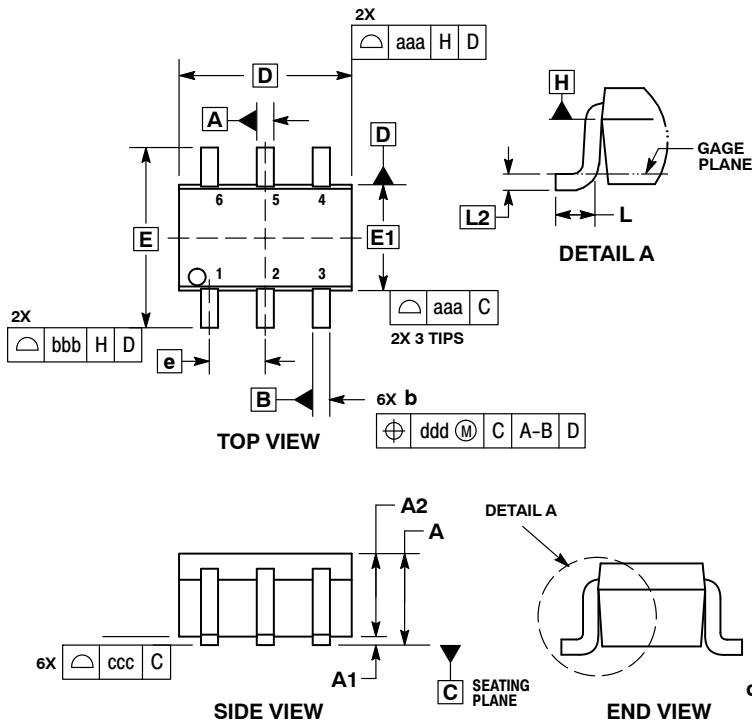


Figure 10. Diode Forward Voltage versus Current

NVJS4151P

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

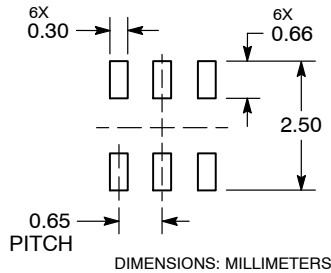


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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